Please cancel claims 97-~~110~~ 104.

105. A method of forming a material adjacent a conductive electrical component comprising:

providing a mass adjacent the conductive electrical component, the mass comprising pores having a size and the mass comprising molecules consisting of silicon and carbon;

forming a layer overlying the mass; and

vaporizing a portion of the mass wherein the vaporizing expands the size of the pores within the mass.

Please cancel claims 106-110.

111. The method of Claim 105, further comprising forming a layer over the mass before the partially vaporizing.

112. The method of Claim 105, further comprising forming a layer over the mass after partially vaporizing.

113. The method of Claim 107, where the conductive material component comprises a pair of conductive lines.

114. The method of Claim 113, further comprising forming at least one support member between the pair of conductive lines.

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115. (New) A method of forming a material adjacent a conductive electrical component comprising:

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providing the conductive electrical component over a substrate;

spinning a liquid onto the substrate and adjacent the conductive electrical component;

at least partially curing the liquid into a substantially self-supporting mass adjacent the conductive electrical component;

anisotropically etching the mass to form a spacer from the mass adjacent the conductive electrical component;

forming a layer overlying the mass; and

at least partially vaporizing the mass.

116. (New) The method of Claim 115, where the liquid comprises two solvents as the liquid is spun onto the substrate, one of the solvents being more volatile than the other, the more volatile solvent being substantially removed by evaporation during the at least partially curing and the other solvent substantially remaining, the other solvent being substantially removed from the mass as the mass is at least partially vaporized, the removing of the other solvent providing the forming of at least one void.

117. (New) The method of Claim 115, where the mass is substantially totally vaporized.

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118. (New) The method of claim 115, where the forming of the layer over the mass comprises forming the layer before at least partially vaporizing the mass.

119. (New) The method of claim 115 wherein the mass comprises polyimide or photoresist.

120. (New) The method of claim 115 wherein the mass is only partially vaporized to leave a matrix adjacent the conductive electrical component, the matrix having at least one void within it.

121. (New) A method of forming an insulative spacer adjacent an electrical component comprising:

providing a mass adjacent the conductive electrical component;

anisotropically etching the mass;

forming a layer of insulative material over the anisotropically etched mass; and

at least partially vaporizing the mass to form at least one void between the layer and the conductive electrical component, the layer and the at least one void together comprising an insulative spacer adjacent the conductive electrical component.

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122. (New) The method of claim 121 wherein the insulative material comprises silicon dioxide.

123. (New) The method of claim 121 wherein the mass comprises carbon.

124. (New) The method of claim 121 wherein the mass is substantially totally vaporized.

125. (New) The method of claim 121 wherein the mass is only partially vaporized.

126. (New) The method of claim 121 wherein the mass comprises polyimide or photoresist.

127. (New) The method of claim 121 wherein the mass comprises SiC_x, wherein x is from about 0.2 to about 1.5.

128. (New) The method of claim 121 wherein the providing the mass comprises a spin-on-wafer technique.

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129. (New) The method of claim 121 wherein the providing the mass comprises a vapor deposition technique.